

**CMXT3904****SURFACE MOUNT SILICON  
DUAL NPN TRANSISTORS**
[www.centrasemi.com](http://www.centrasemi.com)
**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMXT3904 is a dual NPN silicon transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, and designed for small signal general purpose amplifier and switching applications.

**MARKING CODE: X1A****SOT-26 CASE****MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

|                                            | SYMBOL         |             | UNITS              |
|--------------------------------------------|----------------|-------------|--------------------|
| Collector-Base Voltage                     | $V_{CBO}$      | 60          | V                  |
| Collector-Emitter Voltage                  | $V_{CEO}$      | 40          | V                  |
| Emitter-Base Voltage                       | $V_{EBO}$      | 6.0         | V                  |
| Continuous Collector Current               | $I_C$          | 200         | mA                 |
| Power Dissipation                          | $P_D$          | 350         | mW                 |
| Operating and Storage Junction Temperature | $T_J, T_{stg}$ | -65 to +150 | $^\circ\text{C}$   |
| Thermal Resistance                         | $\Theta_{JA}$  | 357         | $^\circ\text{C/W}$ |

**ELECTRICAL CHARACTERISTICS PER TRANSISTOR:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

| SYMBOL        | TEST CONDITIONS                                        | MIN  | MAX  | UNITS      |
|---------------|--------------------------------------------------------|------|------|------------|
| $I_{CEV}$     | $V_{CE}=30\text{V}, V_{EB}=3.0\text{V}$                |      | 50   | nA         |
| $BV_{CBO}$    | $I_C=10\mu\text{A}$                                    | 60   |      | V          |
| $BV_{CEO}$    | $I_C=1.0\text{mA}$                                     | 40   |      | V          |
| $BV_{EBO}$    | $I_E=10\mu\text{A}$                                    | 6.0  |      | V          |
| $V_{CE(SAT)}$ | $I_C=10\text{mA}, I_B=1.0\text{mA}$                    |      | 0.20 | V          |
| $V_{CE(SAT)}$ | $I_C=50\text{mA}, I_B=5.0\text{mA}$                    |      | 0.30 | V          |
| $V_{BE(SAT)}$ | $I_C=10\text{mA}, I_B=1.0\text{mA}$                    | 0.65 | 0.85 | V          |
| $V_{BE(SAT)}$ | $I_C=50\text{mA}, I_B=5.0\text{mA}$                    |      | 0.95 | V          |
| $h_{FE}$      | $V_{CE}=1.0\text{V}, I_C=0.1\text{mA}$                 | 40   |      |            |
| $h_{FE}$      | $V_{CE}=1.0\text{V}, I_C=1.0\text{mA}$                 | 70   |      |            |
| $h_{FE}$      | $V_{CE}=1.0\text{V}, I_C=10\text{mA}$                  | 100  | 300  |            |
| $h_{FE}$      | $V_{CE}=1.0\text{V}, I_C=50\text{mA}$                  | 60   |      |            |
| $h_{FE}$      | $V_{CE}=1.0\text{V}, I_C=100\text{mA}$                 | 30   |      |            |
| $f_T$         | $V_{CE}=20\text{V}, I_C=10\text{mA}, f=100\text{MHz}$  | 300  |      | MHz        |
| $C_{ob}$      | $V_{CB}=5.0\text{V}, I_E=0, f=1.0\text{MHz}$           |      | 4.0  | pF         |
| $C_{ib}$      | $V_{BE}=0.5\text{V}, I_C=0, f=1.0\text{MHz}$           |      | 12   | pF         |
| $h_{ie}$      | $V_{CE}=10\text{V}, I_C=1.0\text{mA}, f=1.0\text{kHz}$ | 1.0  | 10   | k $\Omega$ |

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CMXT3904

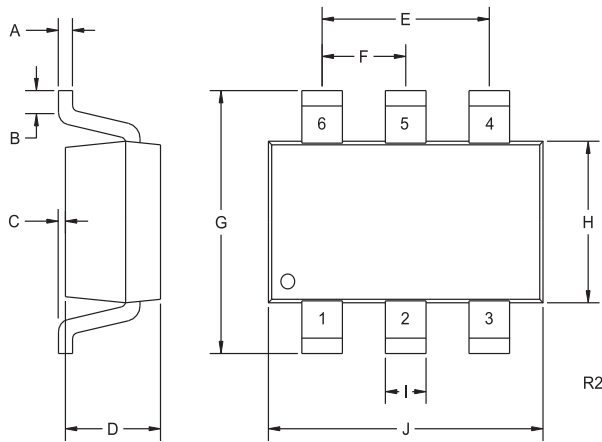
**SURFACE MOUNT SILICON  
DUAL NPN TRANSISTORS**



**ELECTRICAL CHARACTERISTICS PER TRANSISTOR - Continued:** ( $T_A=25^{\circ}\text{C}$  unless otherwise noted)

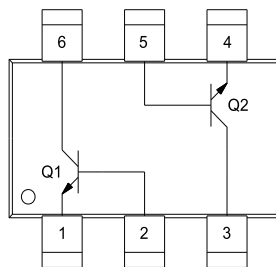
| SYMBOL   | TEST CONDITIONS                                                                                                | MIN | MAX | UNITS            |
|----------|----------------------------------------------------------------------------------------------------------------|-----|-----|------------------|
| $h_{re}$ | $V_{CE}=10\text{V}$ , $I_C=1.0\text{mA}$ , $f=1.0\text{kHz}$                                                   | 0.5 | 8.0 | $\times 10^{-4}$ |
| $h_{fe}$ | $V_{CE}=10\text{V}$ , $I_C=1.0\text{mA}$ , $f=1.0\text{kHz}$                                                   | 100 | 400 |                  |
| $h_{oe}$ | $V_{CE}=10\text{V}$ , $I_C=1.0\text{mA}$ , $f=1.0\text{kHz}$                                                   | 1.0 | 40  | $\mu\text{S}$    |
| NF       | $V_{CE}=5.0\text{V}$ , $I_C=100\mu\text{A}$ , $R_S=1.0\text{k}\Omega$ ,<br>$f=10\text{Hz}$ to $15.7\text{kHz}$ |     | 5.0 | dB               |
| $t_d$    | $V_{CC}=3.0\text{V}$ , $V_{BE}=0.5\text{V}$ , $I_C=10\text{mA}$ , $I_{B1}=1.0\text{mA}$                        |     | 35  | ns               |
| $t_r$    | $V_{CC}=3.0\text{V}$ , $V_{BE}=0.5\text{V}$ , $I_C=10\text{mA}$ , $I_{B1}=1.0\text{mA}$                        |     | 35  | ns               |
| $t_s$    | $V_{CC}=3.0\text{V}$ , $I_C=10\text{mA}$ , $I_{B1}=I_{B2}=1.0\text{mA}$                                        |     | 200 | ns               |
| $t_f$    | $V_{CC}=3.0\text{V}$ , $I_C=10\text{mA}$ , $I_{B1}=I_{B2}=1.0\text{mA}$                                        |     | 50  | ns               |

**SOT-26 CASE - MECHANICAL OUTLINE**



| SYMBOL | DIMENSIONS |       |             |      |
|--------|------------|-------|-------------|------|
|        | INCHES     |       | MILLIMETERS |      |
|        | MIN        | MAX   | MIN         | MAX  |
| A      | 0.004      | 0.007 | 0.11        | 0.19 |
| B      | 0.016      | -     | 0.40        | -    |
| C      | -          | 0.004 | -           | 0.10 |
| D      | 0.039      | 0.047 | 1.00        | 1.20 |
| E      | 0.074      | 0.075 | 1.88        | 1.92 |
| F      | 0.037      | 0.038 | 0.93        | 0.97 |
| G      | 0.102      | 0.118 | 2.60        | 3.00 |
| H      | 0.059      | 0.067 | 1.50        | 1.70 |
| I      | 0.016      |       | 0.41        |      |
| J      | 0.110      | 0.118 | 2.80        | 3.00 |

SOT-26 (REV: R2)



**LEAD CODE:**

- 1) Emitter Q1
- 2) Base Q1
- 3) Collector Q2
- 4) Emitter Q2
- 5) Base Q2
- 6) Collector Q1

**MARKING CODE: X1A**

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## OUTSTANDING SUPPORT AND SUPERIOR SERVICES



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### PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

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### DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2<sup>nd</sup> day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

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### REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

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### CONTACT US

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